SQS407ENW

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Vishay Siliconix

Automotive P-Channel 30 V (D-S) 175 °C MOSFET



Marking code: Q033

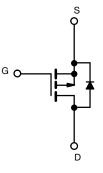
PRODUCT SUMMARY	
V _{DS} (V)	-30
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	0.0108
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.0170
I _D (A)	-16
Configuration	Single
Package	PowerPAK 1212-8W

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified ^d
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unles	s otherwise noted	ł)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	-30	V
Gate-source voltage		V _{GS}	± 20	v
Continuous drain current ^a	T _C = 25 °C		-16	
Continuous drain current "	T _C = 125 °C	ID	-16	
Continuous source current (diode conduction) ^a		I _S	-16	А
Pulsed drain current ^b		I _{DM}	-64	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-23	
Single pulse avalanche energy	L = 0.1 mm	E _{AS}	26.5	mJ
Maximum power dissipation ^b	T _C = 25 °C	PD	62.5	w
Maximum power dissipation	T _C = 125 °C	FD	20	VV
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) e, f			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	81	°C/W
Junction-to-case (drain)		R _{thJC}	2.4	0/10

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing
- e. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8W is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

S18-0633-Rev. A, 25-Jun-2018 1 Document Number: 76627 For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT



SQS407ENW

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SPECIFICATIONS ($T_C = 25 \degree C$, unless otherv	vise noted)					
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	•					•	
Drain-source breakdown voltage	V _{DS}	V _{GS} =	= 0 V, I _D = -250 μA	-30	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = -250 μΑ	-1.5	-2.0	-2.5	
Gate-source leakage	I _{GSS}	V _{DS} =	: 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -30 V	-	-	-1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -30 V, T _J = 125 °C	-	-	-50	μA
		$V_{GS} = 0 V$	V _{DS} = -30 V, T _J = 175 °C	-	-	-150	1
On-state drain current ^a	I _{D(on)}	$V_{GS} = -10 V$	$V_{DS} \le -5 V$	-20	-	-	Α
		$V_{GS} = -10 V$	I _D = -12 A	-	0.0090	0.0108	
Deriver and the second state of the		V _{GS} = -10 V	I _D = -12 A, T _J = 125 °C	-	-	0.0150	
Drain-source on-state resistance ^b	R _{DS(on)}	$V_{GS} = -10 V$	I _D = -12 A, T _J = 175 °C	-	-	0.0180	Ω
		V _{GS} = -4.5 V	I _D = -9 A	-	0.0140	0.0170	
Forward transconductance b	9 _{fs}	V _{DS}	= -15 V, I _D = -7 A	-	34	-	S
Dynamic ^b	•	•				•	
Input capacitance	C _{iss}			-	3515	4572	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = -20 V, f = 1 MHz	-	376	490	pF
Reverse transfer capacitance	C _{rss}			-	358	465	1
Total gate charge ^c	Qg			-	59	77	
Gate-source charge c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -4 \text{ A}$	-	8.6	11.2	nC
Gate-drain charge ^c	Q _{gd}			-	11.5	15	1
Gate resistance	Rg		f = 1 MHz	3	5	8	Ω
Turn-on delay time ^c	t _{d(on)}			-	11.4	15	
Rise time ^c	tr	V _{DD} =	V _{DD} = -15 V, R _I = 3.8 Ω		4	5.3	1
Turn-off delay time ^c	t _{d(off)}	I _D ≅ -4 Å, '	$V_{GEN} = -10 \text{ V}, \text{ R}_{g} = 1 \Omega$	-	62	81	ns
Fall time ^c	t _f	1		-	24	32	1
Source-Drain Diode Ratings and Char	acteristics ^b	•			•	•	
Pulsed current ^a	I _{SM}			-	-	-64	Α
Forward voltage	V _{SD}	I _F =	-8.8 A, V _{GS} = 0 V	-	-0.8	-1.2	V

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

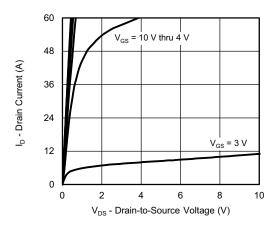
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

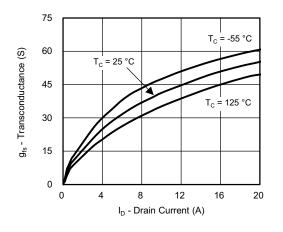
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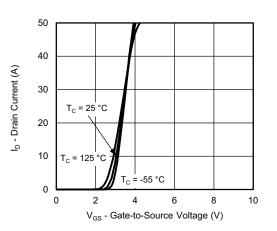
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



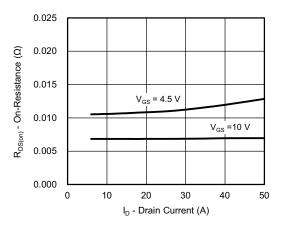
Output Characteristics



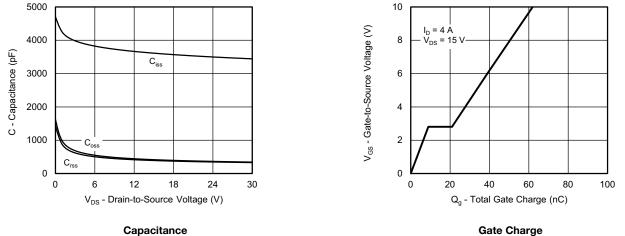
Transconductance



Transfer Characteristics



On-Resistance vs. Drain Current



Capacitance

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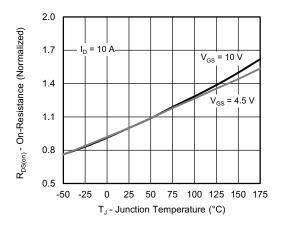
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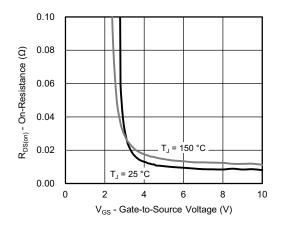
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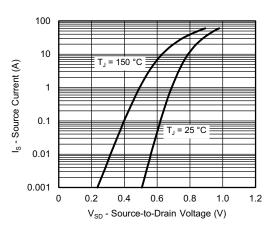
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



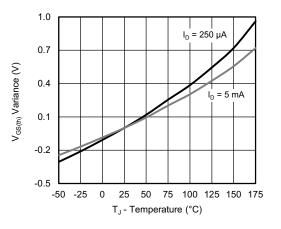
On-Resistance vs. Junction Temperature



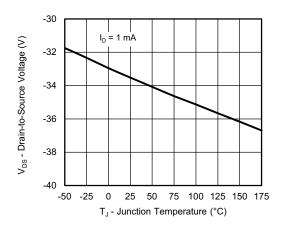
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



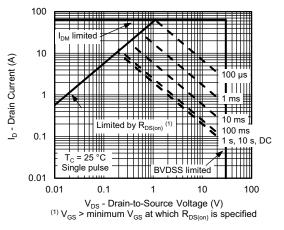
Threshold Voltage



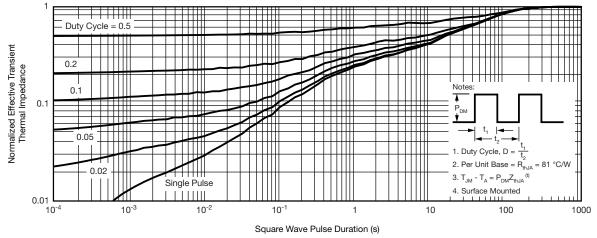
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area

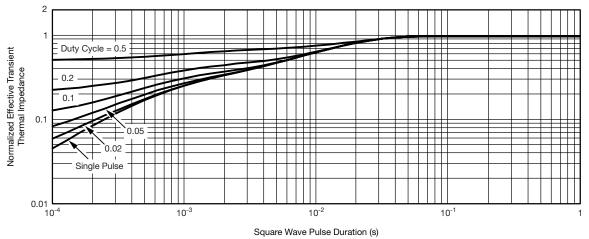


Normalized Thermal Transient Impedance, Junction-to-Ambient

Downloaded from Arrow.com.



THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?76627.

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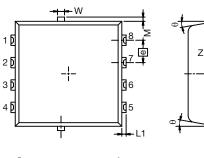
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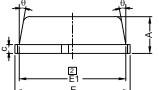


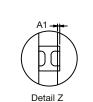
PowerPAK[®] 1212-8W Case Outline

Δ2

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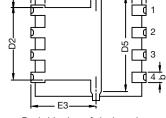




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Б



E2

E4

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 Dimensions exclusive of mold gate burrs
Dimensions exclusive of mold flash and cutting burrs

DIM.	MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0	-	0.05	0	-	0.002	
A2	0	-	0.13	0	-	0.005	
b	0.23	0.30	0.41	0.009	0.012	0.016	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.95	3.05	3.15	0.116	0.120	0.124	
D2	1.98	2.11	2.24	0.078	0.083	0.088	
D4		0.47 typ.			0.0185 typ.		
D5		2.3 typ.			0.090 typ.		
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	2.95	3.05	3.15	0.116	0.120	0.124	
E2	1.47	1.60	1.73	0.058	0.063	0.068	
E3	1.75	1.85	1.98	0.069	0.073	0.078	
E4	0.34 typ.				0.013 typ.		
е		0.65 BSC.			0.026 BSC		
К	0.86 typ.				0.034 typ.		
Н	0.30	0.41	0.51	0.012	0.016	0.020	
L	0.30	0.43	0.56	0.012	0.017	0.022	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М	0.125 typ.			0.005 typ.			
N: C15-1530-R	ev. B, 16-Nov-15						

Backside view of single pad

Notes 1 Inch will govern



RECOMMENDED MINIMUM PADS FOR PowerPAK[®] 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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